

30 V, Dual N-channel Trench MOSFET 15 April 2016

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

| Table 1. Qui | ck reference data | | | | | | |
|---|----------------------------------|---|-----|-----|-----|------|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| Per transistor | | | | | | | , |
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | 30 | V |
| V _{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s | [1] | - | - | 0.95 | А |
| Static characteristics (per transistor) | | | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 0.9 A; T _j = 25 °C | | - | 211 | 252 | mΩ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------|--------------------|-------------------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | S1 | source TR1 | | D1 D2 |
| 2 | G1 | gate TR1 | | |
| 3 | D2 | drain TR2 | | $G1 \xrightarrow{f} G2$ |
| 4 | S2 | source TR2 | | |
| 5 | G2 | gate TR2 | TSSOP6 (SOT363) | |
| 6 | D1 | drain TR1 | | S1 S2 017aaa256 |

6. Ordering information

| Table 3. Ordering in | formation | | |
|----------------------|-----------|--|---------|
| Type number | Package | | |
| | Name | Description | Version |
| PMGD175XNE | TSSOP6 | plastic surface-mounted package; 6 leads | SOT363 |

7. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| | [1] |
| PMGD175XNE | LU% |

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5.Limiting values

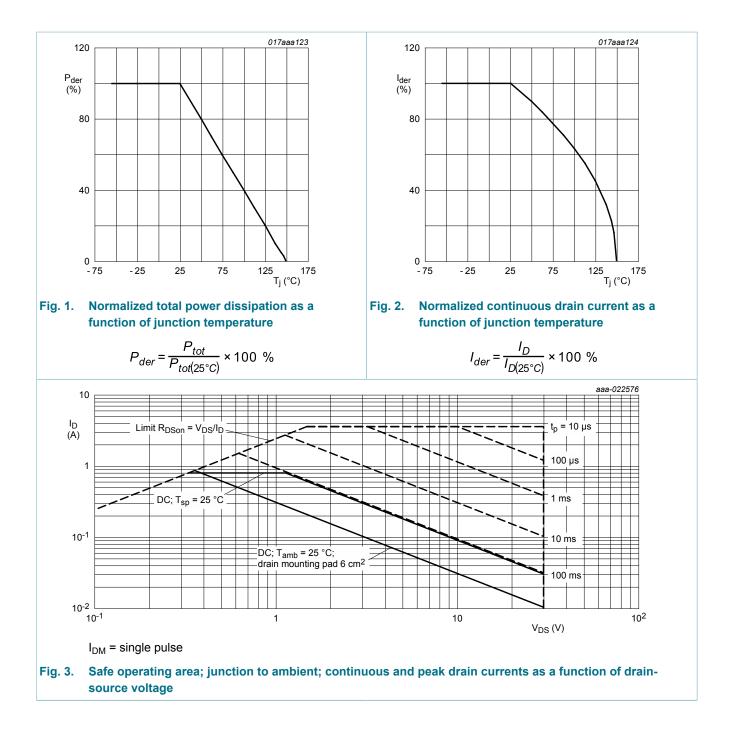
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|------------------|-------------------------|---|------------|-----|------|------|
| Per transis | tor | | | | | |
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 30 | V |
| V _{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s | [1] | - | 0.95 | А |
| | | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | 0.87 | А |
| | | V _{GS} = 4.5 V; T _{amb} = 100 °C | [1] | - | 0.5 | А |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$ | | - | 4 | А |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 260 | m₩ |
| | | | [1] | - | 310 | mΨ |
| | | T _{sp} = 25 °C | | - | 905 | mW |
| Per device | | | | · | · | |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | <u>[2]</u> | - | 390 | m₩ |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | in diode | · · | | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 0.31 | А |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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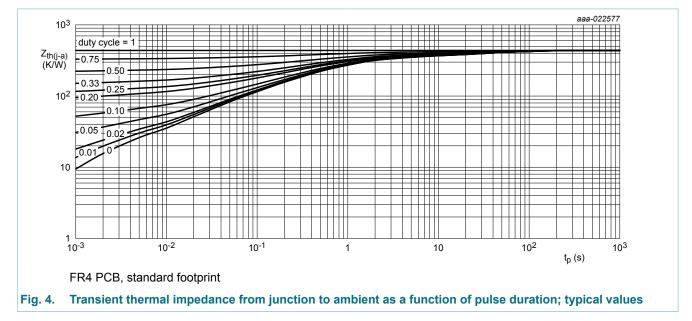
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Thermal characteristics 9.

| Table 6. The | rmal characteristics | | | | | | |
|--|--|----------------------|-----|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
| Per transistor | · | | | | | | _ |
| R _{th(j-a)} thermal resistance from junction to ambient | thermal resistance | | [1] | - | 417 | 480 | K/W |
| | - | | [2] | - | 352 | 405 | K/W |
| | ampient | in free air; t ≤ 5 s | [2] | - | 295 | 340 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 120 | 138 | K/W |
| Per device | | | | | | | |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | [1] | - | - | 320 | K/W |

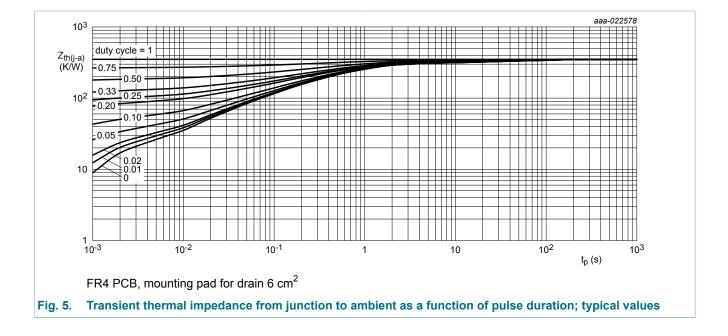
Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1] [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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10. Characteristics

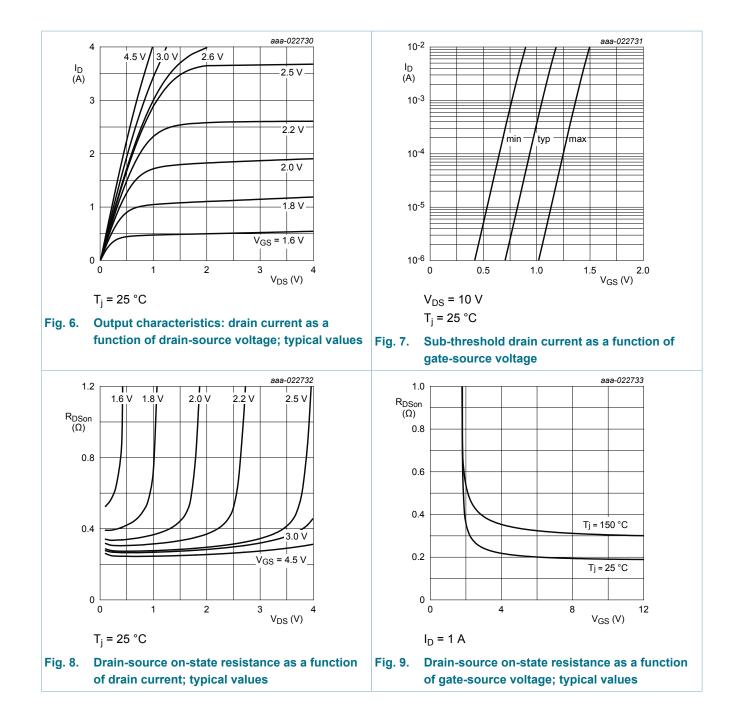
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|---|------|------|------|------|
| Static chara | acteristics (per transistor) | L | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 30 | - | - | V |
| V _{GSth} | gate-source threshold voltage | I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C | 0.75 | 1 | 1.25 | V |
| I _{DSS} | drain leakage current | V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C | - | - | 1 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 10 | μA |
| | | V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -10 | μA |
| | | V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 5 | μA |
| | | V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -5 | μA |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 4.5 V; I _D = 0.9 A; T _j = 25 °C | - | 211 | 252 | mΩ |
| resista | | V _{GS} = 4.5 V; I _D = 0.9 A; T _j = 150 °C | - | 344 | 411 | mΩ |
| | | V _{GS} = 2.5 V; I _D = 0.8 A; T _j = 25 °C | - | 267 | 319 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = 10 V; I _D = 0.9 A; T _j = 25 °C | - | 3.5 | - | S |
| Dynamic ch | aracteristics (per transist | or) | I | | | |
| Q _{G(tot)} | total gate charge | V_{DS} = 15 V; I _D = 0.9 A; V _{GS} = 4.5 V; | - | 1.05 | 1.65 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.15 | - | nC |
| Q _{GD} | gate-drain charge | | - | 0.27 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; | - | 81 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 13 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 9 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 15 V; I _D = 0.9 A; V _{GS} = 4.5 V; | - | 7 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 14 | - | ns |
| t _{d(off)} | turn-off delay time | 1 | - | 17 | - | ns |
| t _f | fall time | 1 | - | 6 | - | ns |
| Source-drai | in diode (per transistor) | 1 | I | | | |
| V _{SD} | source-drain voltage | I _S = 0.3 A; V _{GS} = 0 V; T _i = 25 °C | - | 0.7 | 1.2 | V |

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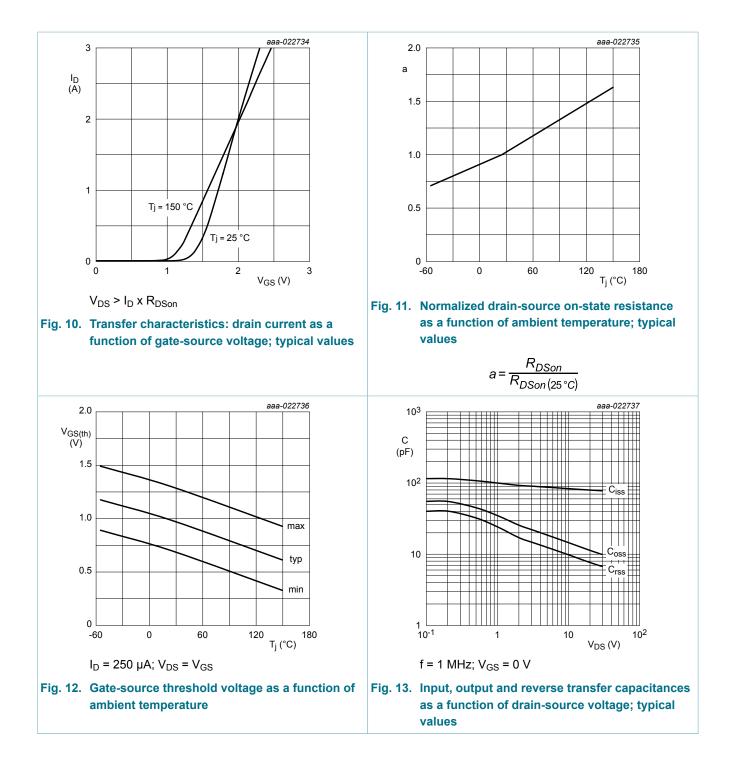
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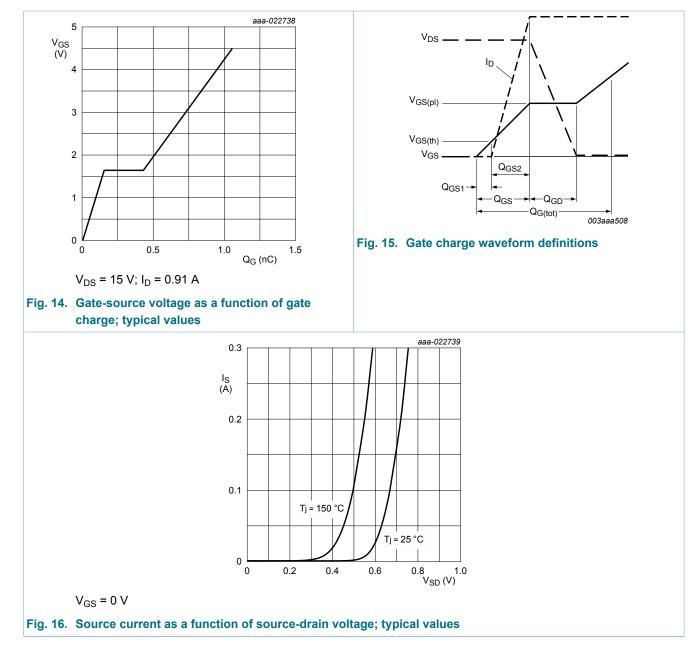
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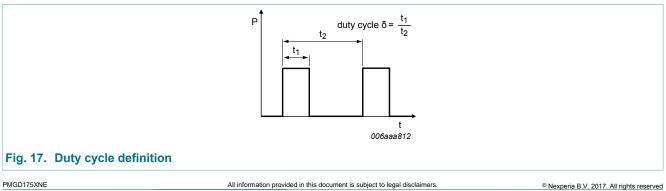
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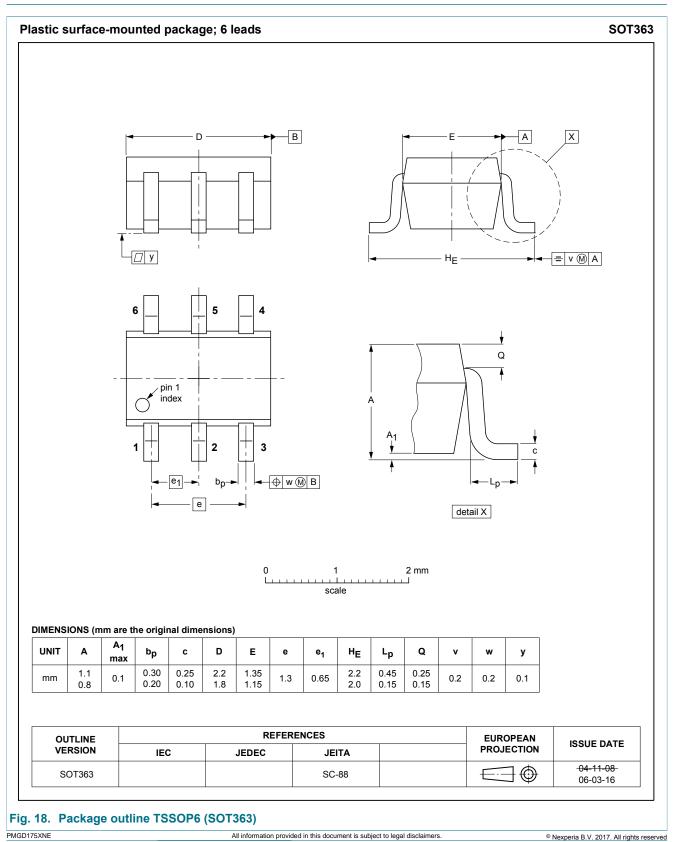


11. Test information



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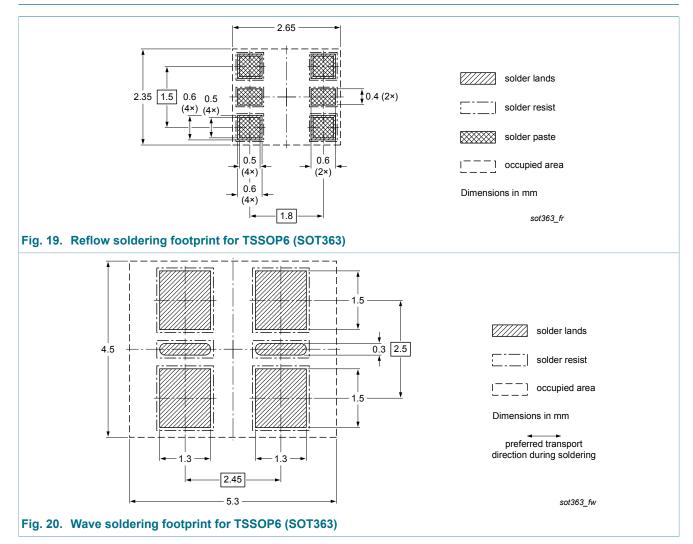
12. Package outline



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13. Soldering



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14. Revision history

| Table 8. Revision his | e 8. Revision history | | | | | | |
|-----------------------|-----------------------|--------------------|---------------|------------|--|--|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | | |
| PMGD175XNE v.1 | 20160415 | Product data sheet | - | - | | | |

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15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [<u>3]</u> | Definition |
|--------------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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